PART B - FEE(S) TRANSMITTAL

Complete and send this form, together with applicable fee(s), to: Mail Stop ISSUE FEE
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

or Fax (571)-273-2885

INSTRUCTIONS: This form should be used for transmitting the ISSUE FEE and PUBLICATION FEE (if required). Blocks 1 through 5 should be completed where appropriate. All further correspondence including the Patent, advance orders and notification of maintenance fees will be mailed to the current correspondence address as indicated unless corrected below or directed otherwise in Block 1, by (a) specifying a new correspondence address; and/or (b) indicating a separate "FEE ADDRESS" for

maintenance fee notifica	tions.		y (a) specifying a new c	201103	pondence address, a	iwor (b) marcaung a sepa	arate FEE ADDRESS for	
CURRENT CORRESPONDENCE ADDRESS (Note: Use Block I for any change of address)				Feet	's) Transmittal This c	ertificate cannot be used t	or domestic mailings of the for any other accompanying ent or formal drawing, must	
24628	7590 02/0	6/2007	A.					
WELSH & KA 120 S RIVERSI 22ND FLOOR CHICAGO, IL 6	PR 2 6 2007	Certificate of Mailing or Transmission I hereby certify that this Fee(s) Transmittal is being deposited with the United States Postal Service with sufficient postage for first class mail in an envelope addressed to the Mail Stop ISSUE FEE address above, or being facsimile transmitted to the USPTO (571) 273-2885, on the date indicated below.						
	B2 00000031 1051202	22	4	G	ERALD T. SHE	KLETON	(Depositor's name)	
01 FC:1501 02 FC:1504		00.00 OP	PADEMARKO	1	oril 23, 200	heles	(Signature) (Date)	
APPLICATION NO.	FILING DATE		FIRST NAMED INVEN					
10/512,022	10/19/2004		Tetsuhiro Iida	nok		TTORNEY DOCKET NO.	CONFIRMATION NO.	
		SILICON PRODUCI		E CR	RYSTAL SILICON V	93120 VAFER PRODUCING M	2202 (ETHOD	
TITLE OF INVENTION: SINGLE CRYSTAL SILICON PRODUCING METHOD, SINGLE CRYSTAL SILICON WAFER PRODUCING METHOD, SEED CRYSTAL FOR PRODUCING SINGLE CRYSTAL SILICON, SINGLE CRYSTAL SILICON INGOT, AND SINGLE CRYSTAL SILICON WAFER								
APPLN. TYPE	SMALL ENTITY	ISSUE FEE DUE	PUBLICATION FEE	OUE	PREV. PAID ISSUE F	EE TOTAL FEE(S) DUE	DATE DUE	
nonprovisional	NO	\$1400	\$300		\$0	\$1700	05/07/2007	
EXAM	INER	ART UNIT	CLASS-SUBCLASS	S	,			
HITESHEW, FI	ELISA CARLA	1722	117-013000					
1. Change of corresponde CFR 1.363).	(1) 46 6.	2. For printing on the patent front page, list (1) the names of up to 3 registered patent attorneys or agents OR, alternatively. WELSH & KATZ, LTD.						
Address form PTO/SI	ondence address (or Cha 3/122) attached.	ange of Correspondence	(2) the name of a	single	firm (having as a me	ember a 2		
"Fee Address" indication (or "Fee Address" Indication form PTO/SB/47; Rev 03-02 or more recent) attached. Use of a Customer Number is required.			registered attorney 2 registered patent	registered attorney or agent) and the names of up to 2 registered patent attorneys or agents. If no name is listed, no name will be printed.				
3. ASSIGNEE NAME A	ND RESIDENCE DATA	A TO BE PRINTED O	N THE PATENT (print o	or typ	e)			
3. ASSIGNEE NAME AND RESIDENCE DATA TO BE PRINTED ON THE PATENT (print or type) PLEASE NOTE: Unless an assignee is identified below, no assignee data will appear on the patent. If an assignee is identified below, the document has been filed for recordation as set forth in 37 CFR 3.11. Completion of this form is NOT a substitute for filing an assignment.								
(A) NAME OF ASSIGNEE (B) RESIDENCE: (CITY and STATE OR COUNTRY)								
SUMCO TECHXIV CORPORATION HIRATSUKA-SHI, KANAGAWA, JAPAN								
Please check the appropriate assignee category or categories (will not be printed on the patent): 🔲 Individual 💆 Corporation or other private group entity 🚨 Government								
4a. The following fee(s) a	are submitted:		4b. Payment of Fee(s): (se first reapply any p	reviously paid issue fee s	hown above)	
•	o small entity discount p	permitted)			l. Form PTO-2038 is	attached.		
Publication Fee (No small entity discount permitted) Advance Order - # of Copies						iciency, or credit any extra copy of this form).		
5. Change in Entity Stat			_					
a. Applicant claims SMALL ENTITY status. See 37 CFR 1.27. b. Applicant is no longer claiming SMALL ENTITY status. See 37 CFR 1.27(g)(2). NOTE: The Issue Fee and Publication Fee (if required) will not be accepted from anyone other than the applicant; a registered attorney or agent; or the assignee or other party in								
interest as shown by the r	ecords of the United Sta	tes Patent and Tradema	ark Office.	an ui	e applicant, a register	d anomey or agent; or the	assignee or other party in	
Authorized Signature Sept 7, Shehlo Date 4/23/07								
Typed or printed name GERALD T. SHEKLETON Registration No. 27,466								
This collection of information is required by 37 CFR 1.311. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, Virginia 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450.								
Inder the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number.								

PATENT





IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Pa	tent Application)
Applicant:	Iida et al.)) Confirmation No. 2202
Serial No.:	10/512,022)
Filed:	October 19, 2004)
For:	Method for Producing Single Crystal Silicon, Method for Producing Single Crystal Silicon Wafer, Seed Crystal for Producing Single Crystal Silicon, Single Crystal Silicon Ingot, and Single Crystal Silicon Wafer)))))
Examiner:	Felisa Carla Hiteshew)
Art Unit:	1722)

ISSUE FEE TRANSMITTAL LETTER

Mail Stop Issue Fee Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Attached is the Issue Fee Transmittal Form No. PTOL-85B, in duplicate, our Check No. 104885 in the amount of \$1,700.00 for the Issue Fee relating to the issuance of the above-identified U.S. patent application under 37 C.F.R. §1.18, and publication.

The Commissioner is authorized to charge payment of any deficiency in the patent issue fee or credit any overpayment to Deposit Account No. 23-0920. A duplicate copy of this transmittal letter is enclosed.

Respectfully submitted,

By Gerald T. Shekleton, Reg. No. 27,466

Date: April 23, 2007

WELSH & KATZ, LTD. 120 South Riverside Plaza, 22nd Floor Chicago, Illinois 60606 Phone (312) 655-1500 Facsimile Number (312) 655-1501

CERTIFICATE OF MAILING OF ISSUE FEE TRANSMITTAL

I hereby certify that this Issue Fee Transmittal Letter, in duplicate, the attached Issue Fee Transmittal Form PTOL-85B, in duplicate, and the attached Issue Fee check relating to the above-identified U.S. patent application, are enclosed together in an envelope being deposited with the United States Postal Service with sufficient postage as First Class Mail addressed to: Mail Stop Issue Fee, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on April 23, 2007.